

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A thin film transistor substrate in a liquid crystal display ~~provided with a data line for applying a data signal, a gate line for applying a gate signal, and a pixel electrode for driving a liquid crystal cell,~~ said substrate comprising:

a data line for applying a data signal to a pixel electrode;

a gate line, disposed substantially perpendicular to said data line for applying a gate signal to said pixel electrode, an extended portion of said gate line providing a gate dummy pattern parallel to said data line ~~formed vertically to the gate line, wherein the gate dummy pattern is formed to overlap with at least one of edge portions~~ portion of the said data line and an edge portion of the pixel electrode.

2. (Canceled)

3. (Currently Amended) The thin film transistor substrate according to claim 1, wherein when the said data line is broken, ~~the~~ said gate dummy pattern is used as a redundancy electrode for electrically connecting ~~the~~ said broken data line.

4. (Currently Amended) The thin film transistor substrate according to claim 3, wherein ~~the~~ said gate dummy pattern ~~is formed to extend integrally from the gate line, and the gate dummy pattern~~ includes a recess formed to permit a repair by disconnection of ~~the~~ said gate dummy pattern from ~~the~~ said gate line.

5. (Currently Amended) The thin film transistor substrate according to claim 1, wherein ~~the~~ said gate dummy pattern is used as a black matrix.

6. (Currently Amended) The thin film transistor substrate according to claim 1, further comprising:

a storage capacitor defined by a ~~horizontal~~ an overlapping part between ~~the~~ said gate line and ~~the~~ said pixel electrode.

7. (Currently Amended) The thin film transistor substrate according to claim 4, further comprising:

a protrusion protruded from ~~the~~ said data line formed in such a manner as to overlap with ~~the~~ said recess, thereby shutting off a light leaked between ~~the~~ said gate dummy pattern and ~~the~~ said gate line.

8. (Currently Amended) The thin film transistor substrate according to claim 1, wherein a gate-insulating layer is formed between ~~the~~ said gate dummy pattern and ~~the~~ said data line.

9. (Currently Amended) The thin film transistor substrate according to claim 4, wherein ~~the~~ said recess is provided at a cutting part for breaking ~~the~~ said gate dummy pattern from ~~the~~ said gate line in such a manner that ~~the~~ said recess is not overlapped with ~~the~~ said broken data line.

10. (Currently Amended) A thin film transistor substrate in a liquid crystal display ~~provided with a data line for applying a data signal, a gate line for applying a gate signal, and a pixel electrode for driving a liquid crystal cell~~, said substrate comprising:

a pixel electrode for driving a liquid crystal cell;

a data line for applying a data signal to said pixel electrode;

a gate line disposed substantially perpendicular to said data line for applying a gate signal to said pixel electrode, an extended portion of said gate line providing a gate dummy pattern parallel to said data line formed vertically to the gate line and to overlap by about 0.5-1  $\mu\text{m}$  with at least one of the an edge portion of said data line and an edge portion of the said pixel electrode, to thereby

serve as a black matrix to shut off light leaked between said data line and said pixel electrode.

11. (Canceled).

12. (Currently Amended) The thin film transistor substrate according to claim 10, wherein when ~~the~~ said data line is broken, ~~the~~ said gate dummy pattern is used as a redundancy electrode for electrically connecting ~~the~~ said broken data line.

13. (Currently Amended) The thin film transistor substrate according to claim 12, wherein ~~the~~ said gate dummy pattern ~~is formed integrally to extend from the gate line, and the gate dummy pattern includes a recess formed to permit a repair by disconnection of~~ said gate dummy pattern from ~~the~~ said gate line.

14. (Canceled)

15. (Currently Amended) The thin film transistor substrate according to claim 10, further comprising:

a storage capacitor defined by a ~~horizontal~~ an overlapping part between ~~the~~ said gate line and ~~the~~ said pixel electrode.

16. (Currently Amended) The thin film transistor substrate according to claim 13, further comprising:

a protrusion formed in such a manner to overlap with ~~the~~ said recess, thereby shutting off a light leaked between ~~the~~ said gate dummy pattern and ~~the~~ said gate line.

17. (Currently Amended) The thin film transistor substrate according to claim 10, wherein a gate-insulating layer is formed between ~~the~~ said gate dummy pattern and ~~the~~ said data line.

18. (Currently Amended) The thin film transistor substrate according to claim ~~10~~ 13, wherein ~~the~~ said recess is provided at a cutting part for breaking ~~the~~ said gate dummy pattern from ~~the~~ said gate line in such a manner that ~~the~~ said recess is not overlapped with ~~the~~ said data line.

19-20. (Canceled)

21. (Currently Amended) The thin film transistor substrate according to claim 1, wherein ~~the~~ said gate dummy pattern is formed to cover substantially all of a gap mostly space between at least one of the edge portions of ~~the~~ said data line

and the an edge portion of the said pixel electrode.

22. (Currently Amended) The thin film transistor substrate according to claim 6, wherein ~~the gate dummy pattern is formed to extend integrally from the gate line, and wherein~~ an overlap portion of the said gate dummy pattern and the an edge portion of the said pixel electrode with ~~the~~ a gate insulating layer therebetween, forms an auxiliary storage capacitor.

23. (Currently Amended) The thin film transistor substrate according to claim 10, wherein ~~the~~ said gate dummy pattern is formed to cover substantially all of a gap ~~mostly space~~ between at least one of the edge portions of the said data line and the an edge portion of the said pixel electrode.

24. (Currently Amended) The thin film transistor substrate according to claim 15, wherein ~~the gate dummy pattern is formed to extend integrally from the gate line, and wherein~~ an overlap portion of the said gate dummy pattern and the an edge portion of the pixel electrode with ~~the~~ a gate insulating layer therebetween, forms an auxiliary storage capacitor.

25. (Currently Amended) A thin film transistor substrate for a display device ~~including a data line extending in a first direction, a gate line extending in a~~

~~second direction and crossing the data line, and pixel electrodes,~~ the thin film transistor substrate comprising:

a data line disposed in a first direction;

a gate line disposed in a second direction which crosses the first direction,  
a protruded portion of said gate line being disposed parallel to said data line to  
form a gate dummy pattern splitting off into ~~including~~ first and second extension  
parts extending from ~~the~~ said gate line in the first direction and separated from  
each other, ~~the~~ said first extension part disposed below a first edge portion of ~~the~~  
said data line and a side portion of an adjacent pixel electrode, ~~the~~ said second  
extension part disposed below a second edge portion of ~~the~~ said data line and a  
side portion of another adjacent pixel electrode, ~~the~~ said first and second edge  
portions being opposite edge portions of ~~the~~ said data line.